



# RF Power Transistors

40608

RCA-40608 is an epitaxial silicon n-p-n planar transistor. It is especially designed for operation as a Class A, wide-band power amplifier in VHF circuits.

The features of high gain-bandwidth product and low cross-modulation make the 40608 especially suited for use in CATV and MATV systems.

\*Formerly RCA Dev. Type No. TA2761

**MAXIMUM RATINGS, Absolute-Maximum Values:**

COLLECTOR-TO-BASE VOLTAGE . . . $V_{CBO}$	40	V
COLLECTOR-TO-EMITTER VOLTAGE: With external base-to-emitter resistance, ( $R_{BE}$ ) = 100 $\Omega$ . . . . . $V_{CER}$	40	V
EMITTER-TO-BASE VOLTAGE . . . . . $V_{EBO}$	2	V
COLLECTOR CURRENT . . . . . $I_C$	0.4	A
TRANSISTOR DISSIPATION . . . . . $P_T$ At case temperatures up to 25 $^{\circ}$ C . . . . .	3.5	W
At case temperatures above 25 $^{\circ}$ C . . . . . See Fig. 1.		
TEMPERATURE RANGE: Storage & Operating (Junction) . . . . .	-65 to +200	$^{\circ}$ C
LEAD TEMPERATURE (During soldering): At distances $\geq$ 1/32 in. (0.79 mm) from seating plane for 10 s max. . . . .	230	$^{\circ}$ C

## SILICON N-P-N "overlay" TRANSISTOR

For Class A Wide-Band  
CATV and MATV  
Applications



JEDEC TO-39

**Features:**

- o High Gain-Bandwidth Product
- o Low Cross-Modulation

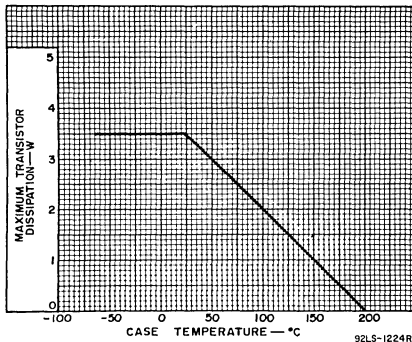
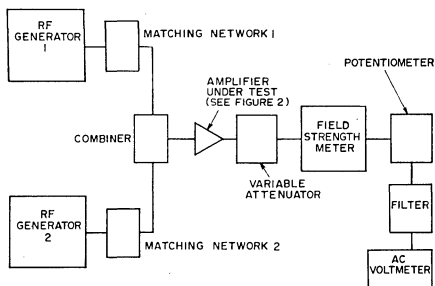


Fig. 1 - Dissipation Derating Curve

## ELECTRICAL CHARACTERISTICS, Case Temperature = 25°C

Characteristic	Symbol	Test Conditions					Limits		Units
		DC Collector Volts		DC Current (mA)			Min.	Max.	
		V <sub>CB</sub>	V <sub>CE</sub>	I <sub>E</sub>	I <sub>B</sub>	I <sub>C</sub>			
Collector-Cutoff Current	I <sub>CEO</sub>		20	0	0		100	μA	
Collector-to-Base Breakdown Voltage	V <sub>(BR)CBO</sub>			0		0.1	40	V	
Collector-to-Emitter Voltage (Sustaining)	V <sub>CER(sus)</sub>					50 <sup>a</sup>	40	V	
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>			0.1		0	2	V	
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>			10	50		1.0	V	
Collector-to-Base Capacitance (Measured at 1MHz)	C <sub>ob</sub>	30		0			3.0	pF	
Gain-Bandwidth Product	f <sub>T</sub>		15			50	700	MHz	
DC Forward-Current Transfer Ratio	h <sub>FE</sub>		15			50	35	120	
Voltage Gain (See Fig. 2.)	VG		15			50	11	dB	
Cross Modulation @ 46 dBmV (See Fig. 3.)	CM		15			50	-57 (Typ.)	dB	

<sup>a</sup> Pulsed through an inductor (20 mH); duty factor = 50%; R<sub>BE</sub> = 100 Ω.



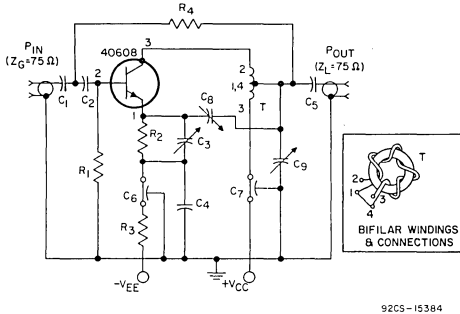
92LS-1225RI

Generator No. 1 & No. 2: Hewlett-Packard, HP608D, or equivalent  
 Matching Network No. 1 & No. 2: 50 to 75 Ω  
 Combiner: 20 dB isolation between generators  
 Variable Attenuator: As required  
 Field Strength Meter, with Detector Output: 50-220 MHz  
 Potentiometer: 100 kΩ  
 Filter: 1000 Hz  
 AC Voltmeter: Ballantine 861, or equivalent

## OPERATING INSTRUCTIONS FOR CROSS-MODULATION TEST

1. Set up equipment as shown in Fig. 2.
2. Set generator No. 1 to 150 MHz modulated 30% by 1000 Hz, and tune field strength meter to 150 MHz.
3. Adjust output of generator No. 1 to give rated output of the amplifier.
4. Adjust potentiometer to calibrate voltmeter for a convenient level. This level then corresponds to 100% cross modulation.
5. Remove modulation.
6. Set generator No. 2 to 210 MHz modulated 30% by 1000 Hz and tune field strength meter to 210 MHz.
7. Adjust output of generator No. 2 to give rated output of the amplifier. (If the amplifier has a flat response then the output of the two signal generators will be equal.)
8. Tune field strength meter to 150 MHz CW and read voltmeter.
9. Turn voltmeter to proper scale for reading. Calculate percentage of cross modulation based upon 100% level set in step 4.

Fig. 2-Block Diagram for Cross-Modulation Test Set-Up



- C<sub>1</sub>, C<sub>2</sub>, C<sub>5</sub>: 0.002 μF
- C<sub>3</sub>: 7-100 pF, ARCO 423, or equivalent
- C<sub>4</sub>: .03 μF
- C<sub>6</sub>, C<sub>7</sub>: 1,500 pF
- C<sub>8</sub>, C<sub>9</sub>: 8-60 pF, ARCO 404, or equivalent
- R<sub>1</sub>: 390 Ω, ½ W
- R<sub>2</sub>: 6.8 Ω, ½ W
- R<sub>3</sub>: 330 Ω, 1 W
- R<sub>4</sub>: 270 Ω, ½ W
- T: 4 turns No. 30 wire, bifilar wound; toroidal core: 3/8 in. OD, 3/16 in. ID, 1/8 in. thick, IGC\* type Q-1, or equivalent.

\*Indiana General Corp., Electronics/Ferrites Div., Kearsbey, N.J.

Fig. 3-RF Amplifier Circuit for Voltage Gain Test

TYPICAL ADMITTANCE CHARACTERISTICS  
(Common-Emitter Circuit)

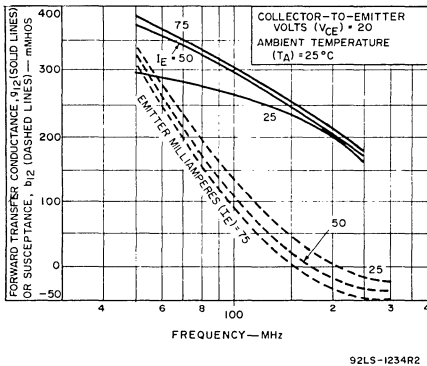


Fig. 4-Forward Transfer Admittance

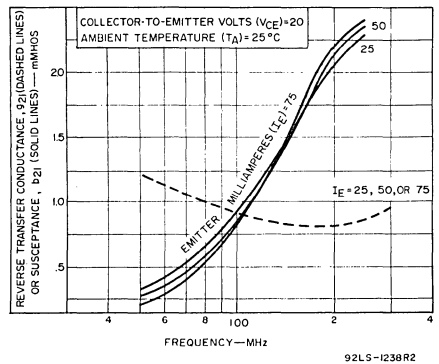


Fig. 5-Reverse Transfer Admittance

TYPICAL ADMITTANCE CHARACTERISTICS

(Common-Emitter Circuit)

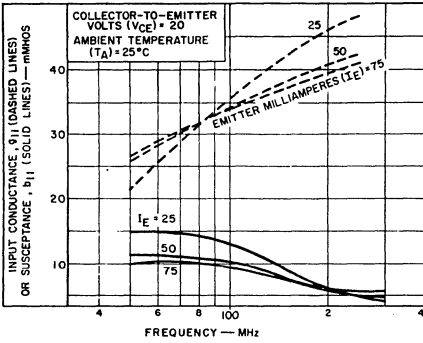


Fig. 6 - Input Admittance

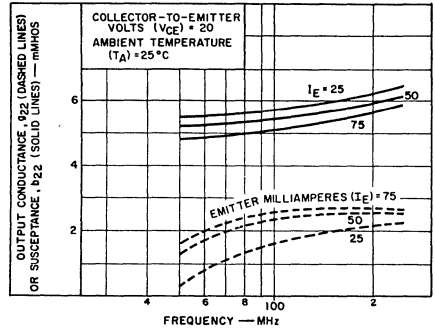


Fig. 7 - Output Admittance

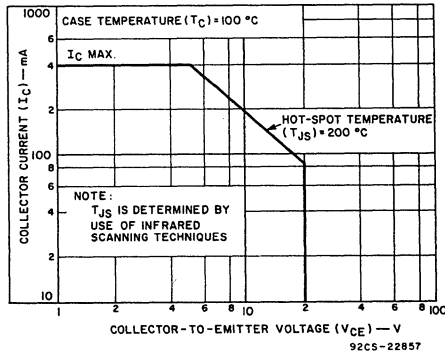


Fig. 8 - Safe Area for DC Operation

TERMINAL CONNECTIONS

- Lead 1 - Emitter
- Lead 2 - Base
- Lead 3 - Collector, Case